

Silicon NPN Power Transistors

2SC4386

DESCRIPTION

- With TO-3PML package
- Complement to type 2SA1671

APPLICATIONS

- Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

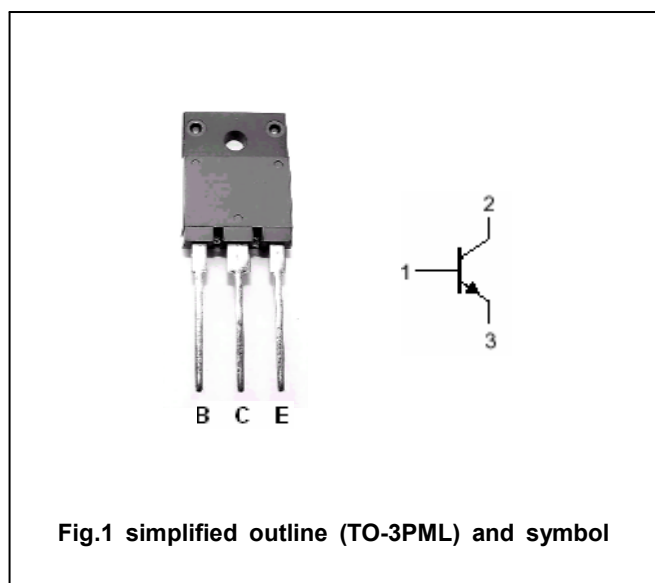


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	160	V
V_{CEO}	Collector-emitter voltage	Open base	120	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		8	A
I_B	Base current		4	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	75	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA; I _B =0	120			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3 A; I _B =0.3 A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =160V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =3A ; V _{CE} =4V	50		180	
f _T	Transition frequency	I _E =-0.5A ; V _{CE} =12V		20		MHz

◆ h_{FE} classifications

O	P	Y
50-100	70-140	90-180

